

**100mW High Power Laser Diode**

**Description**

The SLD301XT is a gain-guided, high-power laser diode with a built-in TE cooler. A new flat, square package with a low thermal resistance and an in-line pin configuration is employed.

Fine tuning of the wavelength is possible by controlling the laser chip temperature.

**Features**

- High power  
Recommended power output  $P_o = 90\text{mW}$
- Low operating current
- Newly developed flat package with built-in TE cooler, thermistor, and photodiode.

**Applications**

- Solid state laser excitation
- Medical use

**Structure**

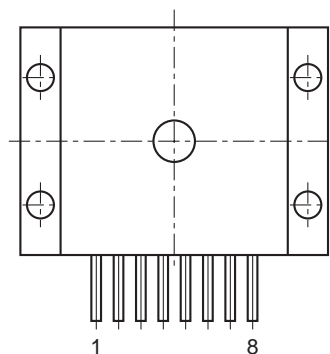
GaAlAs double-hetero-type laser diode

**Absolute Maximum Ratings (T<sub>th</sub> = 25°C)**

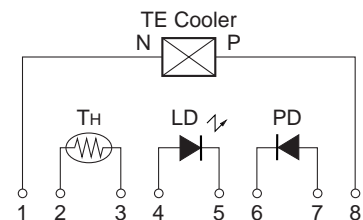
• Optical power output	P <sub>o</sub>		100	mW
• Reverse voltage	V <sub>R</sub>	LD	2	V
		PD	15	V
• Operating temperature (T <sub>th</sub> )	T <sub>opr</sub>		-10 to +50	°C
• Storage temperature	T <sub>stg</sub>		-40 to +85	°C
• Operating current of TE cooler	I <sub>T</sub>		2.5	A

**Pin Configuration (Top View)**

No.	Function
1	TE cooler, negative
2	Thermistor lead 1
3	Thermistor lead 2
4	Laser diode anode
5	Laser diode cathode
6	Photodiode cathode
7	Photodiode anode
8	TE cooler, positive



**Equivalent Circuit**



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**Electrical and Optical Characteristics**

(Tth: Thermistor temperature, Tth = 25°C)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Threshold current	Ith			150	200	mA
Operating current	Iop	P <sub>O</sub> = 90mW		250	400	mA
Operating voltage	Vop	P <sub>O</sub> = 90mW		1.9	3.0	V
Wavelength*1	λp	P <sub>O</sub> = 90mW	770		840	nm
Monitor current	I <sub>mon</sub>	P <sub>O</sub> = 90mW V <sub>R</sub> = 10V		0.15		mA
Radiation angle (F. W. H. M.*)	Perpendicular	θ <sub>⊥</sub>	P <sub>O</sub> = 90mW	28	40	degree
	Parallel	θ <sub>//</sub>		12	17	degree
Positional accuracy	Position	ΔX, ΔY	P <sub>O</sub> = 90mW		±100	μm
	Angle	Δφ <sub>⊥</sub>			±3	degree
Differential efficiency	η <sub>D</sub>	P <sub>O</sub> = 90mW	0.65	0.9		mW/mA
Thermistor resistance	R <sub>th</sub>	T <sub>th</sub> = 25°C		10		kΩ

\* F. W. H. M. : Full Width at Half Maximum

**\*1 Wavelength Selection Classification**

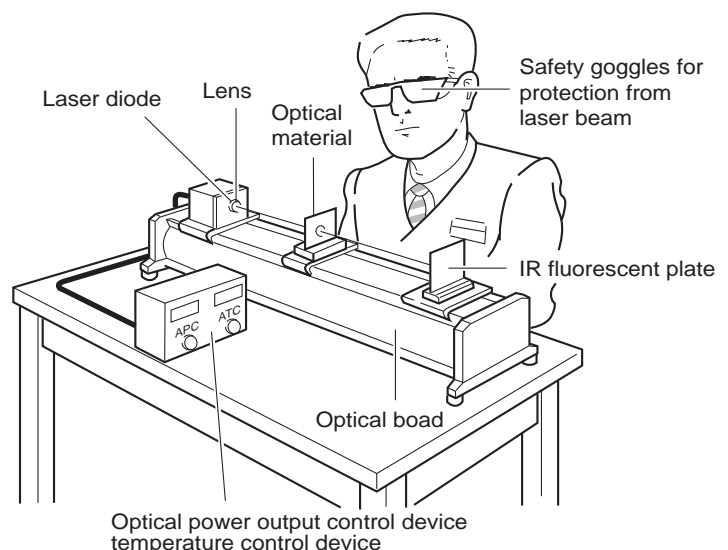
Type	Wavelength (nm)
SLD301XT-1	785 ± 15
SLD301XT-2	810 ± 10
SLD301XT-3	830 ± 10

Type	Wavelength (nm)
SLD301XT-21	798 ± 3
SLD301XT-24	807 ± 3
SLD301XT-25	810 ± 3

**Handling Precautions**

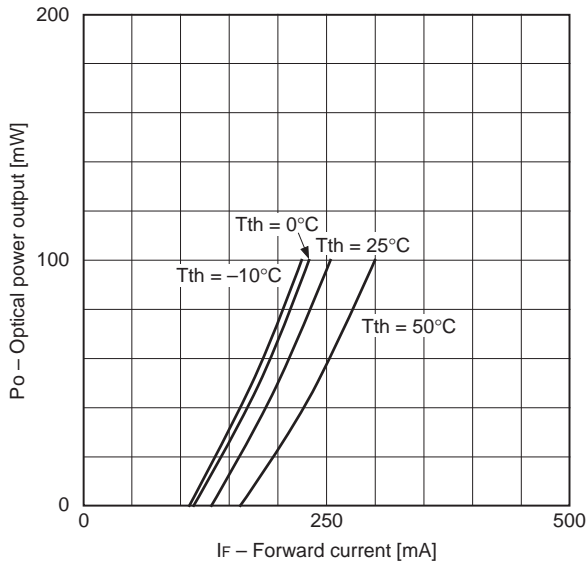
**Eye protection against laser beams**

The optical output of laser diodes ranges from several mW to 1W. However the optical power density of the laser beam at the diode chip reaches 1mW/cm<sup>2</sup>. Unlike gas lasers, since laser diode beams are divergent, uncollimated laser diode beams are fairly safe at a laser diode. For observing laser beams, ALWAYS use safety goggles that block infrared rays. Usage of IR scopes, IR cameras and fluorescent plates is also recommended for monitoring laser beams safely.

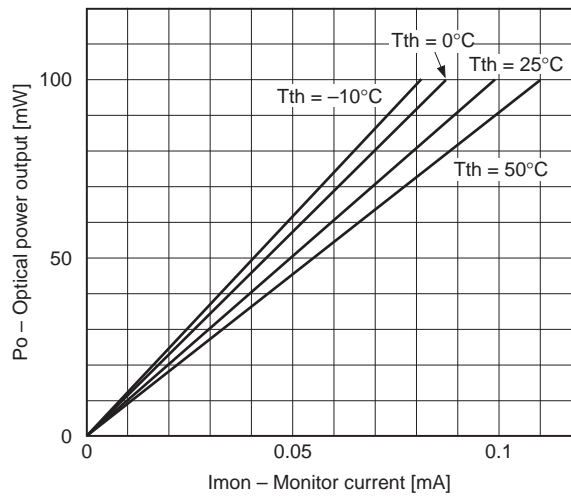


Example of Representative Characteristics

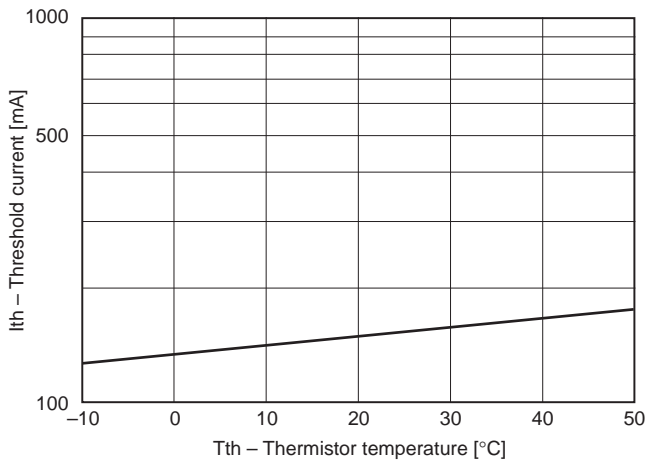
Optical power output vs. Forward current characteristics



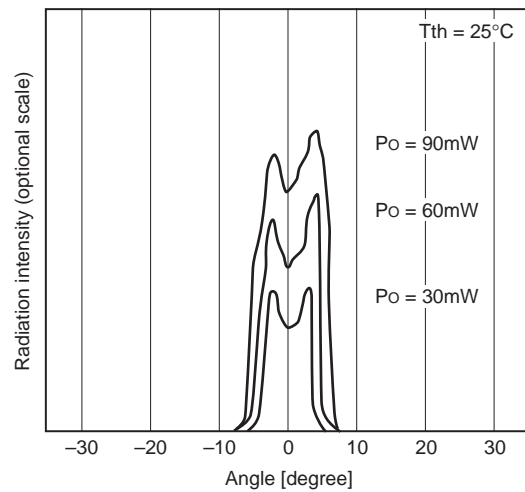
Optical power output vs. Monitor current characteristics



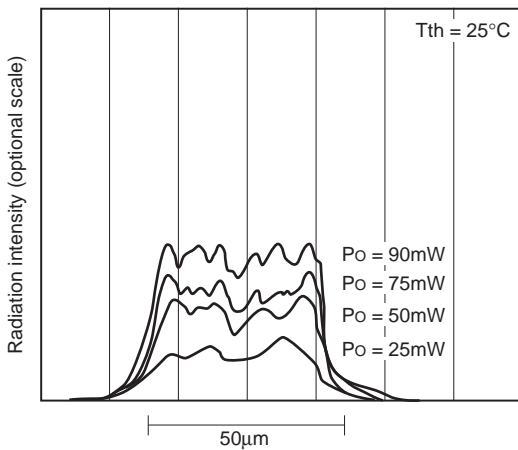
Threshold current vs. Temperature characteristics



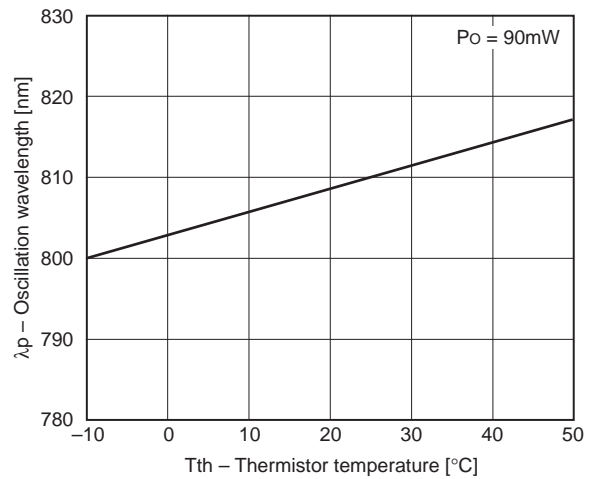
Power dependence of far field pattern (parallel to junction)



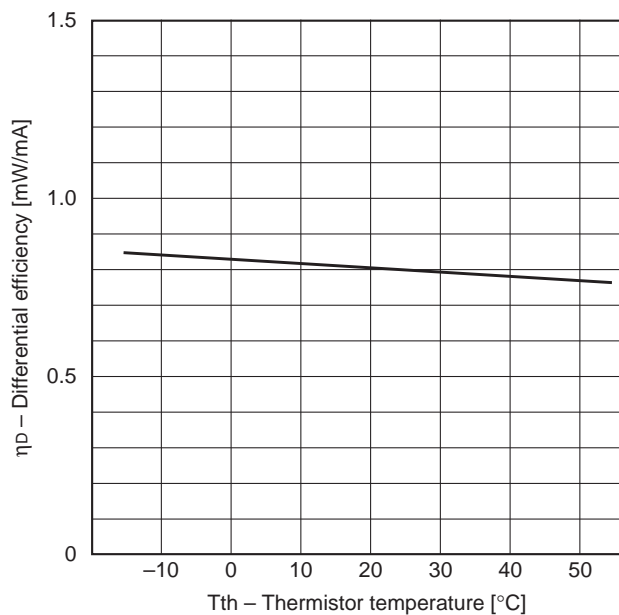
Power dependence of near field pattern



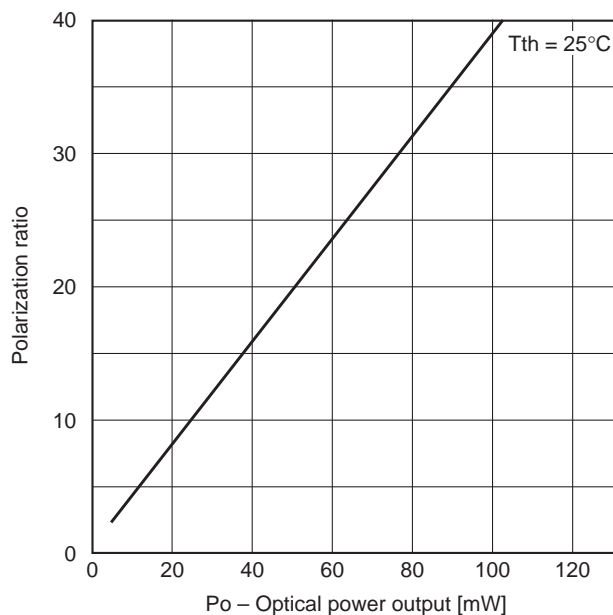
Oscillation wavelength vs. Temperature characteristics



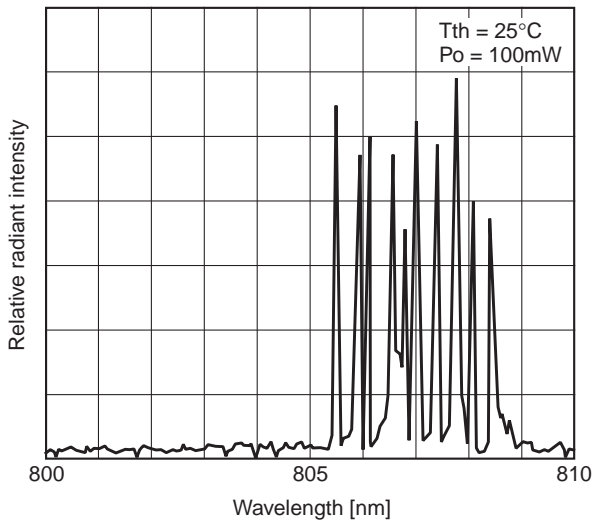
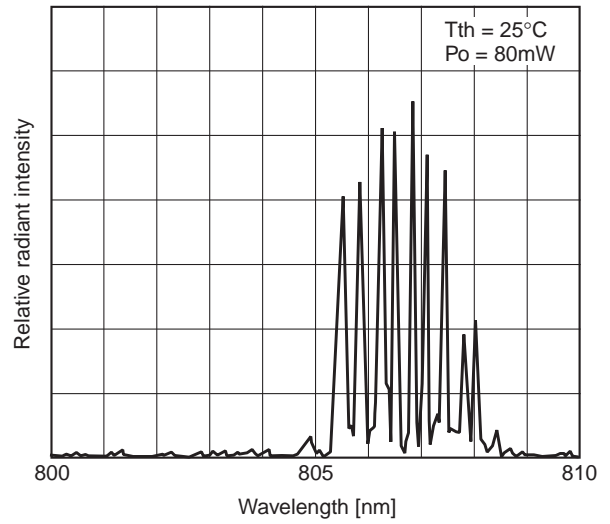
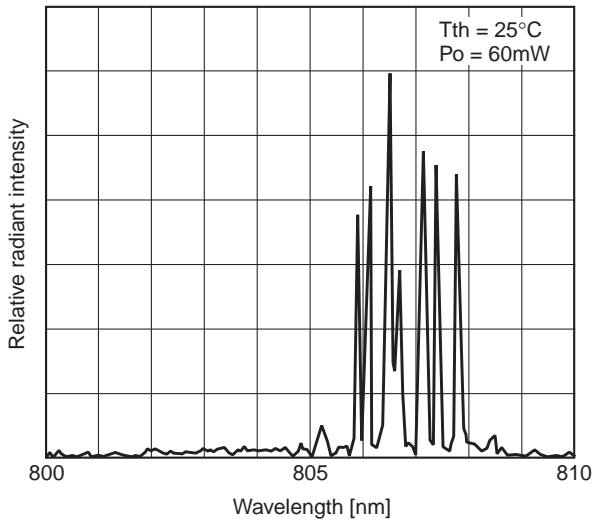
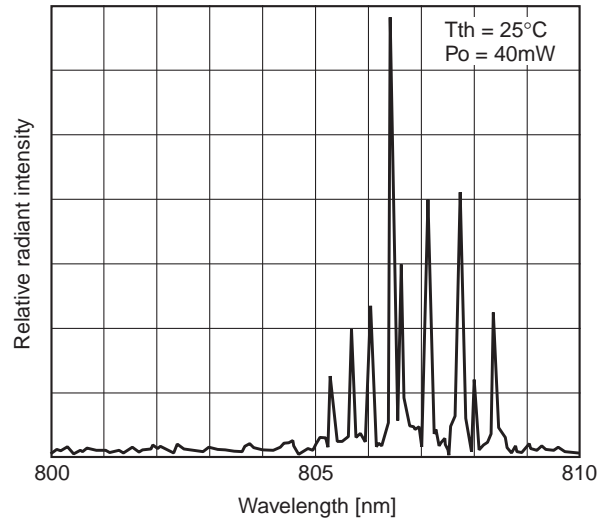
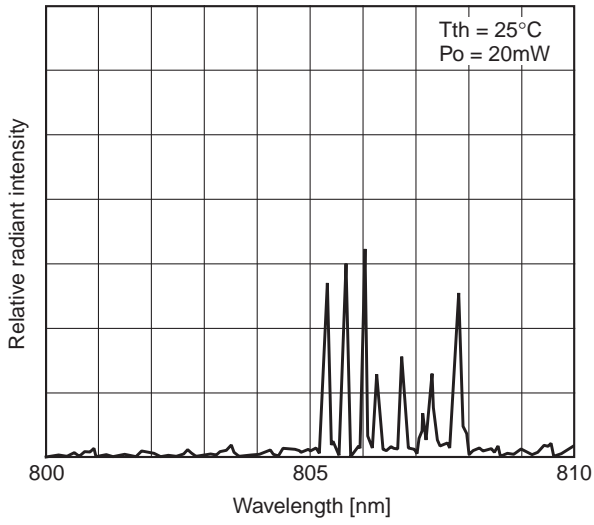
Differential efficiency vs. Temperature characteristics



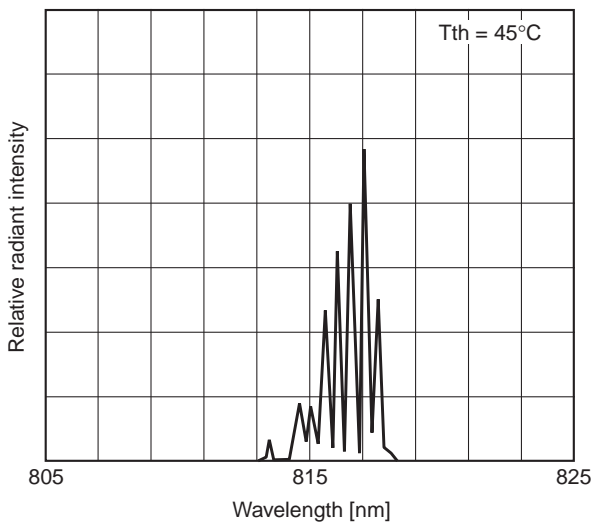
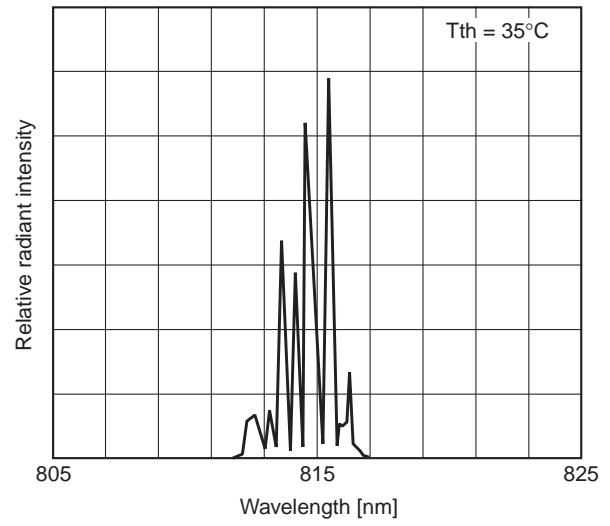
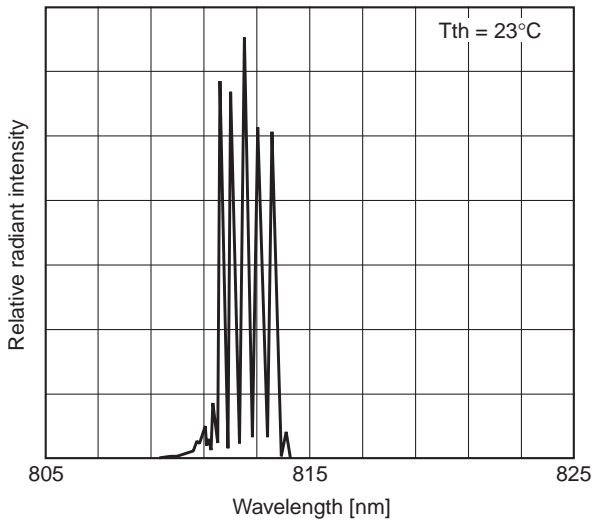
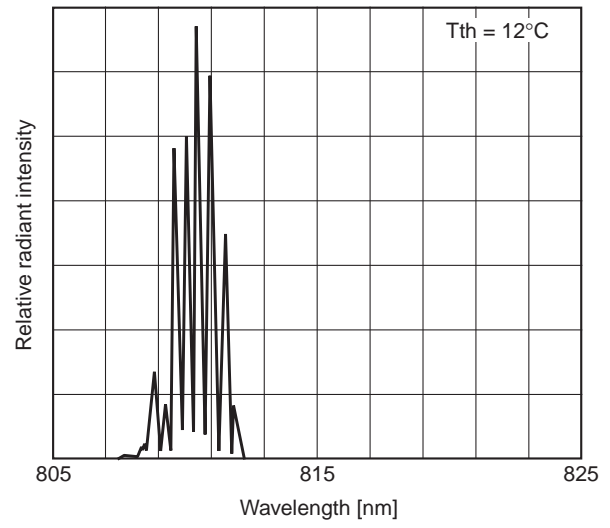
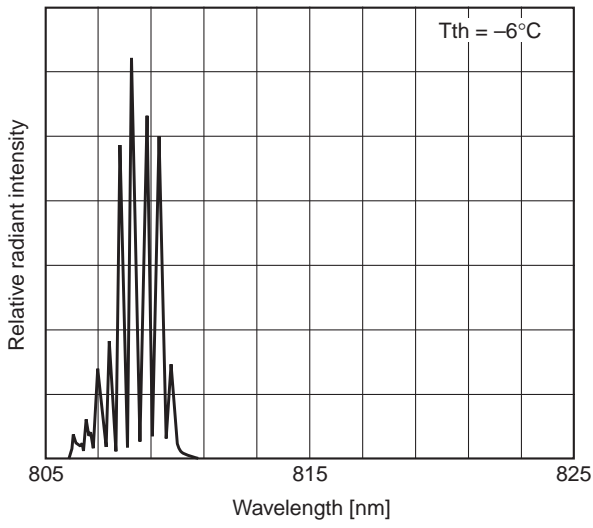
Power dependence of polarization ratio



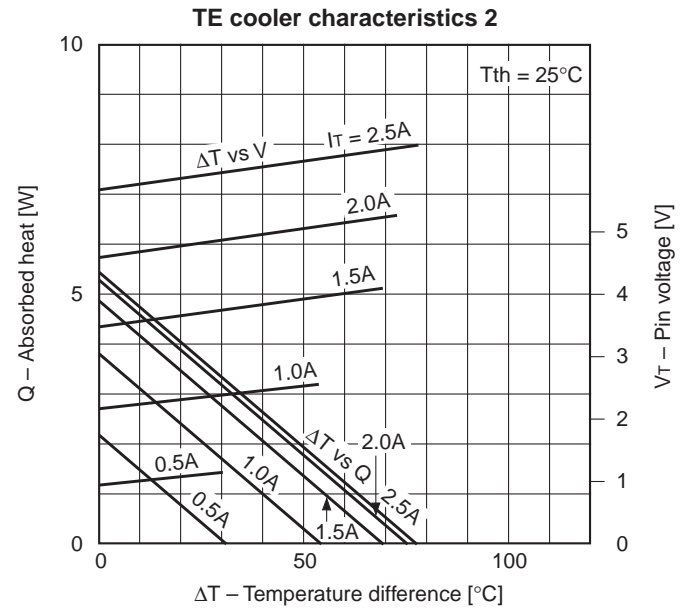
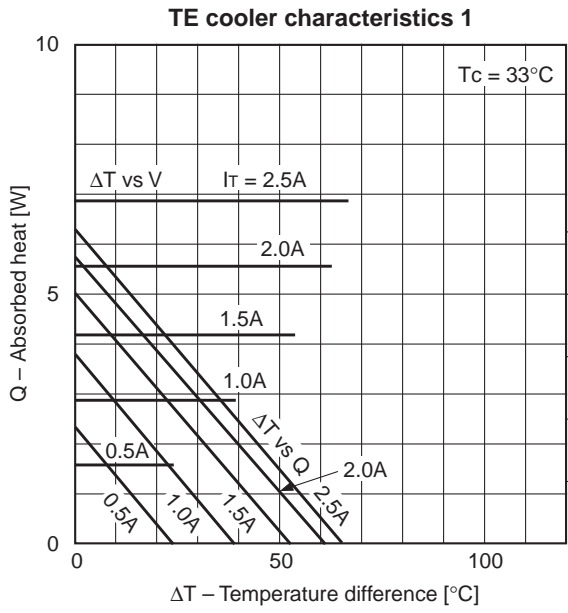
Power dependence of wavelength



Temperature dependence of wavelength ( $P_o = 90\text{mW}$ )

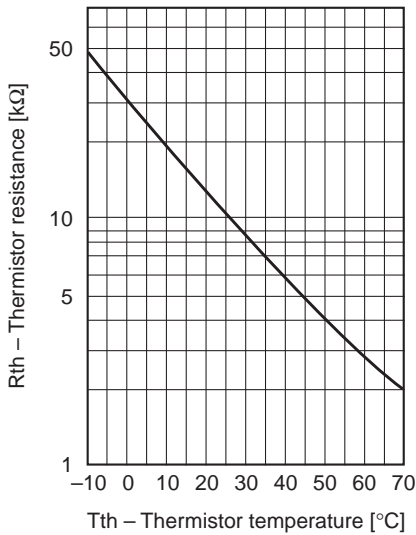


TE cooler characteristics



$\Delta T$  :  $T_c - T_{th}$   
 $T_{th}$  : Thermistor temperature  
 $T_c$  : Case temperature

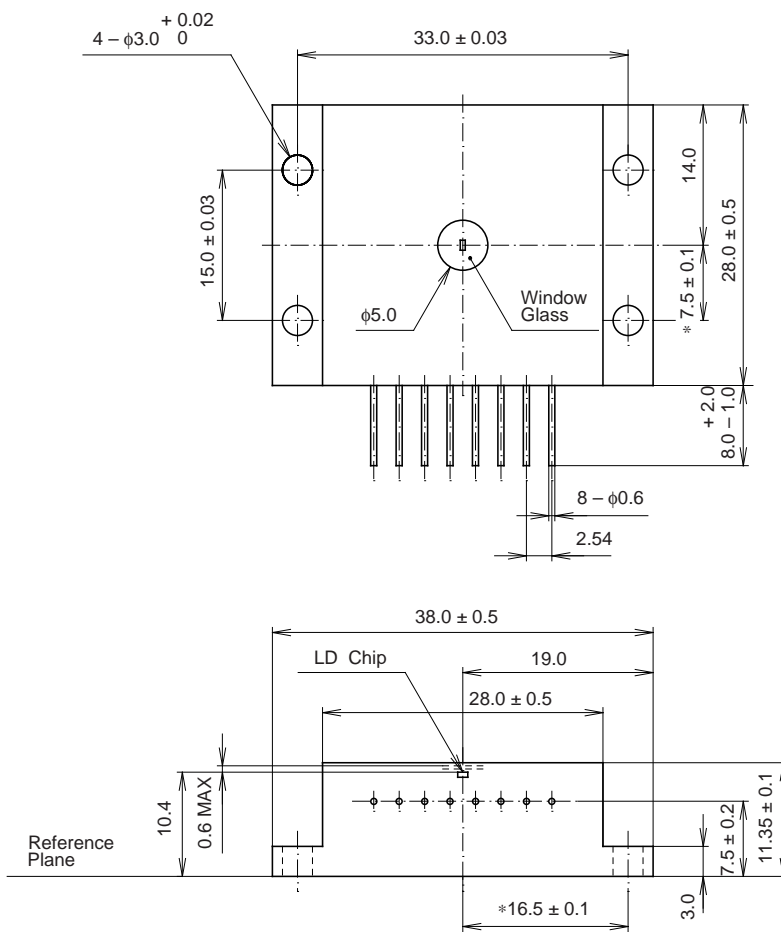
Thermistor characteristics



Package Outline

Unit: mm

M-247 (LO-10)



\*Distance between pilot hole and emitting area

SONY CODE	M-247
EIAJ CODE	_____
JEDEC CODE	_____

PACKAGE WEIGHT	4.3g
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